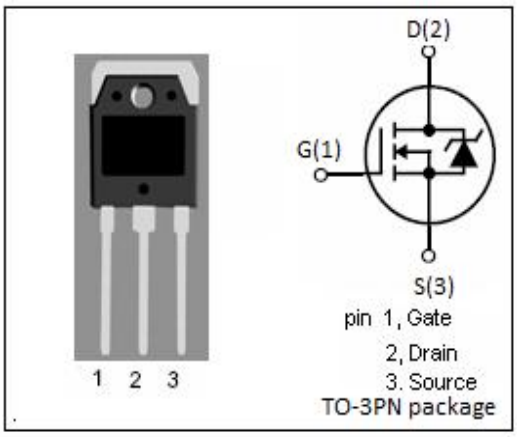
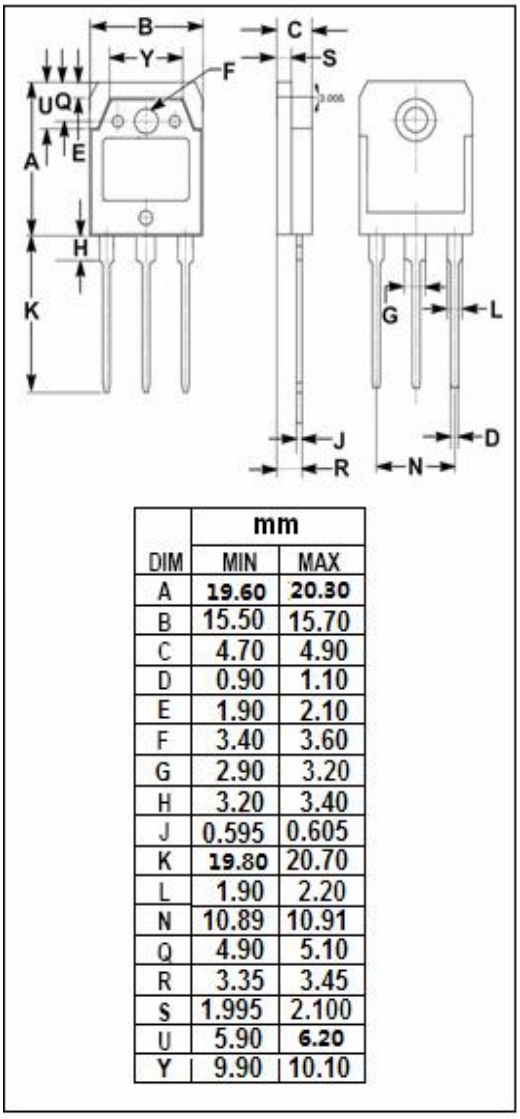
isc N-Channel MOSFET Transistor STHV102



- **FEATURES**
- With TO-3PN packaging
- High speed switching
- Standard level gate drive
- Easy to use
- 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

- **APPLICATIONS**
- Power supply
- Switching applications



DIM	mm MIN	mm MAX
A	19.60	20.30
B	15.50	15.70
C	4.70	4.90
D	0.90	1.10
E	1.90	2.10
F	3.40	3.60
G	2.90	3.20
H	3.20	3.40
J	0.595	0.605
K	19.80	20.70
L	1.90	2.20
N	10.89	10.91
Q	4.90	5.10
R	3.35	3.45
S	1.995	2.100
U	5.90	6.20
Y	9.90	10.10

- **ABSOLUTE MAXIMUM RATINGS(T_a=25℃)**

SYMBOL	PARAMETER	VALUE	UNIT
V_{DSS}	Drain-Source Voltage	1000	V
V_{GSS}	Gate-Source Voltage	±20	V
I_D	Drain Current-Continuous @Tc=25℃ Tc=100℃	4.2 2.6	A
I_{DM}	Drain Current-Single Pulsed	16	A
P_D	Total Dissipation	150	W
T_j	Operating Junction Temperature	-65~150	℃
T_{stg}	Storage Temperature	-65~150	℃

- **THERMAL CHARACTERISTICS**

SYMBOL	PARAMETER	MAX	UNIT
Rth(ch-c)	Channel-to-case thermal resistance	0.83	℃/W
Rth(ch-a)	Channel-to-ambient thermal resistance	30	℃/W

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ELECTRICAL CHARACTERISTICS

T_C=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP	MAX	UNIT
BV_{DSS}	Drain-Source Breakdown Voltage	V_{GS}=0V; I_D= 0.25mA	1000			V
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS}=V_{GS}; I_D=0.25mA	2.0		4.0	V
$R_{DS(on)}$	Drain-Source On-Resistance	V_{GS}= 10V; I_D=2A		3.1	3.5	Ω
I_{GSS}	Gate-Source Leakage Current	V_{GS}= ±20V;V_{DS}= 0V			±0.1	μA
I_{DSS}	Drain-Source Leakage Current	V_{DS}= 1000V; V_{GS}= 0v;Tj=25℃ V_{DS}= 800V; V_{GS}= 0v;Tj=125℃			25 250	μA
V_{SDF}	Diode forward voltage	I_{SD}=4.2A, V_{GS} = 0 V			2	V